

Description

The GM76C88AL is a 65,536 bit static random access memory organized as 8,192 words by 8 bits using CMOS technology and operated from a single 5V supply. Advanced circuit techniques provide low power feature with a maximum operating current of 40mA and standby current of max 100 μ A. Its very low standby power requirement makes it ideal for applications requiring nonvolatile storage with back-up batteries. The asynchronous and static nature of the memory requires no external clock or refreshing circuits.

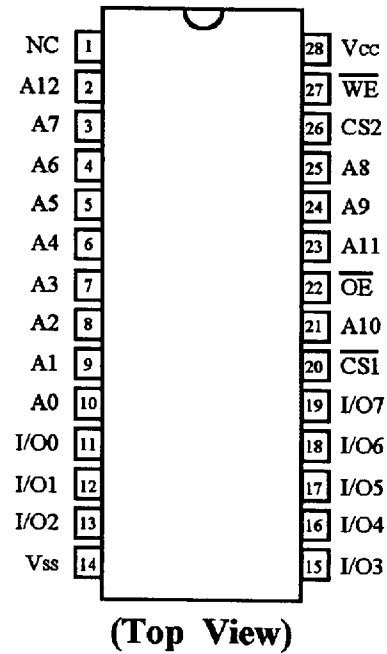
Features

- Fast Access Time : 120/150ns
- Low Power Operation
 Standby : 2 μ A (Typ)
 Operation : 25mA (Typ)
- Completely Static RAM : No Clock or Timing Strobe Required
- Non-Volatile Storage with Back-up Batteries
- 3-State Output with Wired-OR Capability
- Directly TTL Compatible : All Inputs and Outputs
- Single Power Supply (5V \pm 10%)
- Standard 28 DIP, SOP and S-DIP

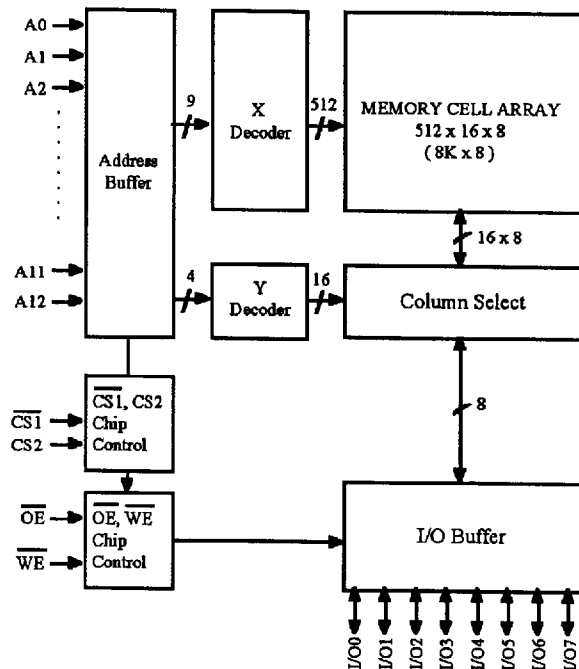
Pin Description

Pin	Function
A0-A12	Address Inputs
\overline{WE}	Write Enable Input
$\overline{CS1}$, CS2	Chip Select
\overline{OE}	Output Enable
I/O0-I/O7	Data Input/Output
Vcc	Power Supply (+5V)
Vss	Ground
NC	No Connection

Pin Configuration



Block Diagram



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
T _A	Ambient Temperature under Bias	0 ~ 70	°C
T _{STG}	Storage Temperature	-65 ~ 150	°C
T _{SOL}	Soldering Temperature and Time	260, 10 (at lead)	°C, S
V _{CC}	Supply Voltage	-0.5 ~ 7.0	V
V _{IN}	Input Voltage	-0.5 ~ 7.0	V
P _d	Power Dissipation	1.0	W

Recommended Operating Conditions (T_A = 0 ~ 70°C)

Symbol	Parameter	Min	Typ	Max	Unit
V _{CC}	Supply Voltage	4.5	5.0	5.5	V
V _{IH}	Input High Voltage	2.2	-	V _{CC} + 0.5	V
V _{IL}	Input Low Voltage	-0.5	-	0.8	V

Truth Table

$\overline{CS1}$	CS2	\overline{OE}	\overline{WE}	A0 to A12	DATA I/O	MODE
H	X	X	X	-	Hi-Z	Standby
X	L	X	X	-	Hi-Z	
L	H	X	L	Stable	Input Data	Write
L	H	L	H	Stable	Output Data	Read
L	H	H	H	Stable	Hi-Z	Output Disable

*Note: X means don't care.

DC Electrical Characteristics (V_{CC} = 5V ± 10%, T_A = 0 ~ 70°C)

Symbol	Parameter	Conditions	Min	*Typ	Max	Unit	
V _{OH}	Output High Voltage	I _{OH} = -1.0mA	2.4	V _{CC} -0.1	-	V	
V _{OL}	Output Low Voltage	I _{OL} = 4.0mA	-	0.2	0.4	V	
I _{I(L)}	Input Leakage Current	V _I = 0 to V _{CC}	-	-	1	μA	
I _{O(L)}	Output Leakage Current	$\overline{CS1} = V_{IH}$ or CS2 = V _{IL} or $\overline{WE} = V_{IL}$ or OE = V _{IH} , V _{IO} = 0 to V _{CC}	-	-	1	μA	
I _{CC1}	Operating Supply Current	V _I = V _{IL} , V _{IH} I _{VO} = 0mA	trc = 1μs	-	6	10	mA
I _{CC2}			tpc = Min	-	25	40	
		V _I = 0.2V/V _{CC} -0.2V I _{VO} = 0mA	trc = 1μs	-	3	5	mA
tpc = Min			-	20	35		
I _{CCS1}	Standby Power Supply Current	$\overline{CS1} = V_{IH}$ or CS2 = V _{IL}	-	1.5	3	mA	
I _{CCS2}		$\overline{CS1} = CS2 \geq V_{CC}-0.2V$ or CS2 ≤ 0.2V	-	2	100	μA	

*TYP. Values are measured at 25°C, V_{CC} = 5V

AC Electrical Characteristics (V_{CC} = 5V ± 10%, T_A = 0 ~ 70°C)

Read Cycle

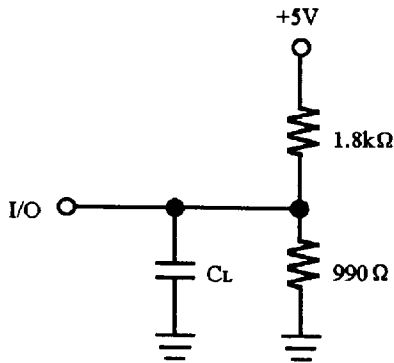
Symbol	Parameter	Conditions	GM76C88AL-12		GM76C88AL-15		Unit
			Min	Max	Min	Max	
t _{RC}	Read Cycle Time	*1	120	-	150	-	ns
t _{AA}	Address Access Time		-	120	-	150	ns
t _{ACS1}	Chip Select 1 Access Time		-	120	-	150	ns
t _{ACS2}	Chip Select 2 Access Time		-	120	-	150	ns
t _{OE}	Output Enable Access Time		-	60	-	70	ns
t _{OH}	Output Hold Time		30	-	30	-	ns
t _{CLZ1}	Chip Select 1 Output Setup Time	*2	10	-	10	-	ns
t _{CHZ1}	Chip Select 1 Output Floating		-	60	-	70	ns
t _{CLZ2}	Chip Select 2 Output Setup Time		10	-	10	-	ns
t _{CHZ2}	Chip Select 2 Output Floating		-	60	-	70	ns
t _{OLZ}	Output Enable Output Setup Time		5	-	5	-	ns
t _{OHZ}	Output Enable Output Floating		-	55	-	60	ns

Write Cycle

Symbol	Parameter	Conditions	GM76C88AL-12		GM76C88AL-15		Unit
			Min	Max	Min	Max	
t _{WC}	Write Cycle Time	*1	120	-	150	-	ns
t _{CW1}	Chip select Time 1		100	-	120	-	ns
t _{CW2}	Chip Select Time 2		100	-	120	-	ns
t _{AW}	Address Enable Time		100	-	120	-	ns
t _{AS}	Address Setup Time		0	-	0	-	ns
t _{WP}	Write Pulse Width		85	-	100	-	ns
t _{WR}	Address Hold Time		0	-	0	-	ns
t _{DW}	Input Data Setup Time		50	-	60	-	ns
t _{DH}	Input Data Hold Time		0	-	0	-	ns
t _{WHZ}	R/W Output Floating		*2	-	60	-	70
t _{OW}	R/W Output Setup Time	10		-	10	-	ns

***1 Test Conditions.**

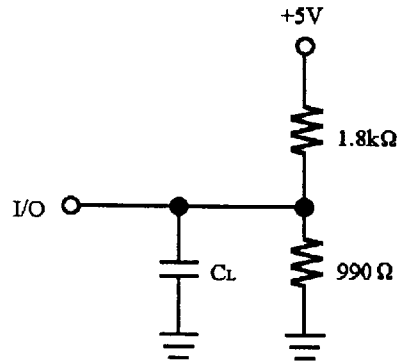
1. Input pulse level : 0.8V to 2.2V
2. $t_r = t_f = 5\text{ns}$
3. Input/output timing reference level : 1.5V
4. Output load : 1TTL + 100pF



$C_L = 100\text{pF}$ (Includes Jig Capacitance)

***2 Test Conditions.**

1. Input pulse level : 0.8V to 2.2V
2. $t_r = t_f = 10\text{ns}$
3. Input timing reference level : 1.5V
4. Output timing reference levels : $\pm 200\text{mV}$ (the level displace from stable output voltage level)
5. Output load : 1TTL + 5pF



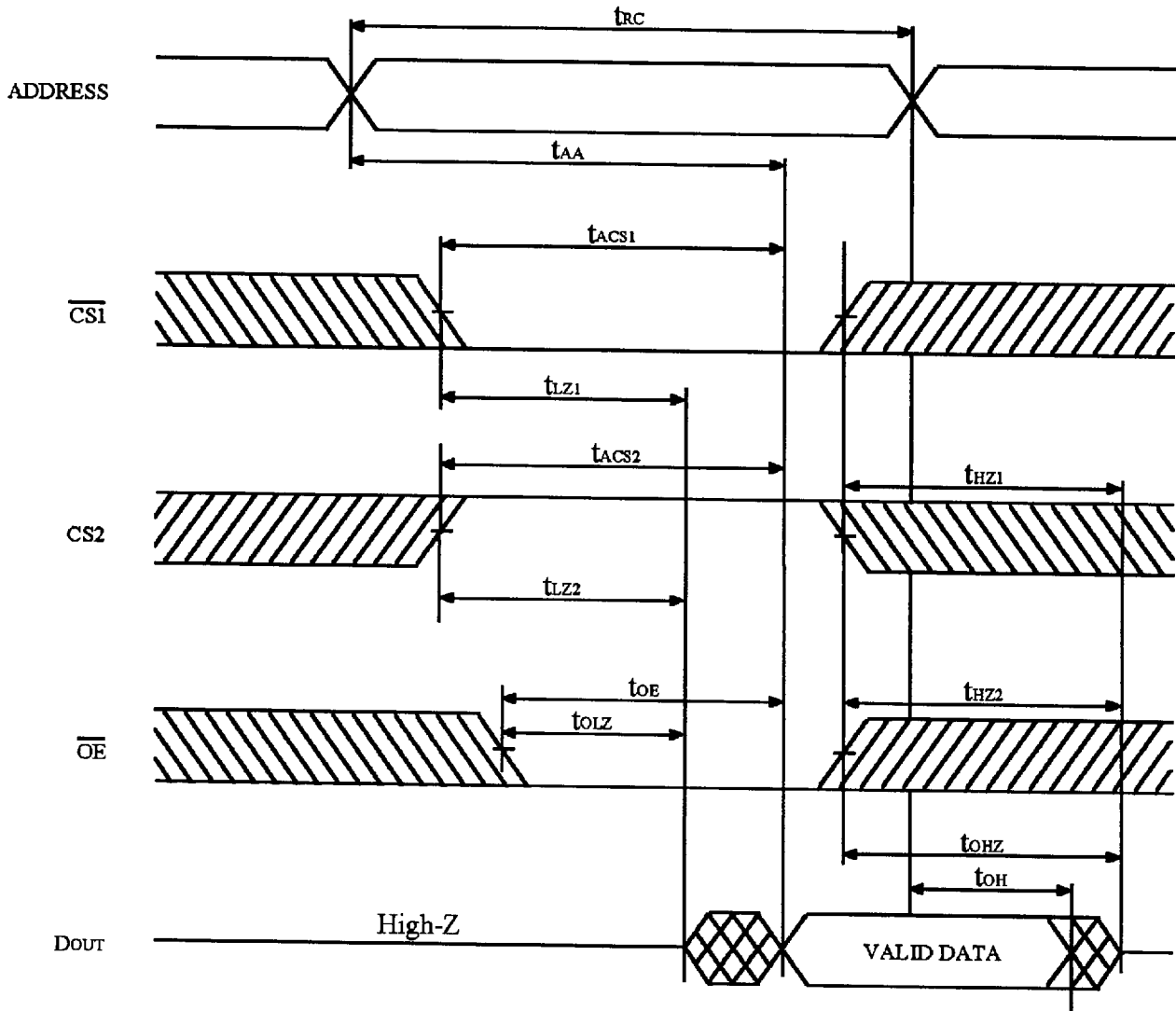
$C_L = 5\text{pF}$ (Includes Jig Capacitance)

Capacitance ($f = 1\text{MHz}$, $T_A = 25^\circ\text{C}$)

Symbol	Parameter	Test Conditions	Min	Max	Unit
C_{IN}	Input Capacitance	$V_I = 0\text{V}$	-	6	pF
C_{OUT}	Output Capacitance	$V_O = 0\text{V}$	-	8	pF

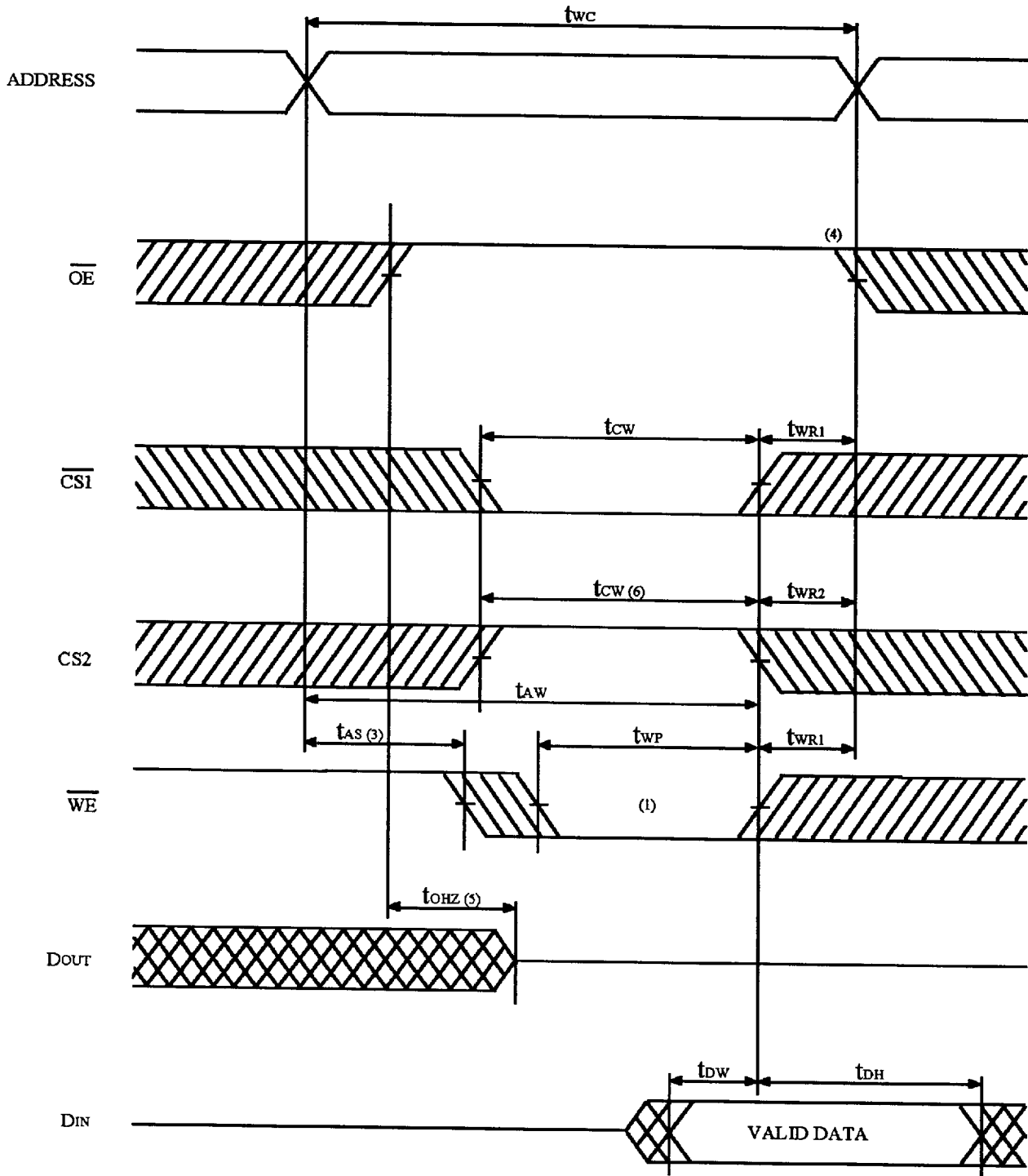
Timing Waveforms

Read Cycle

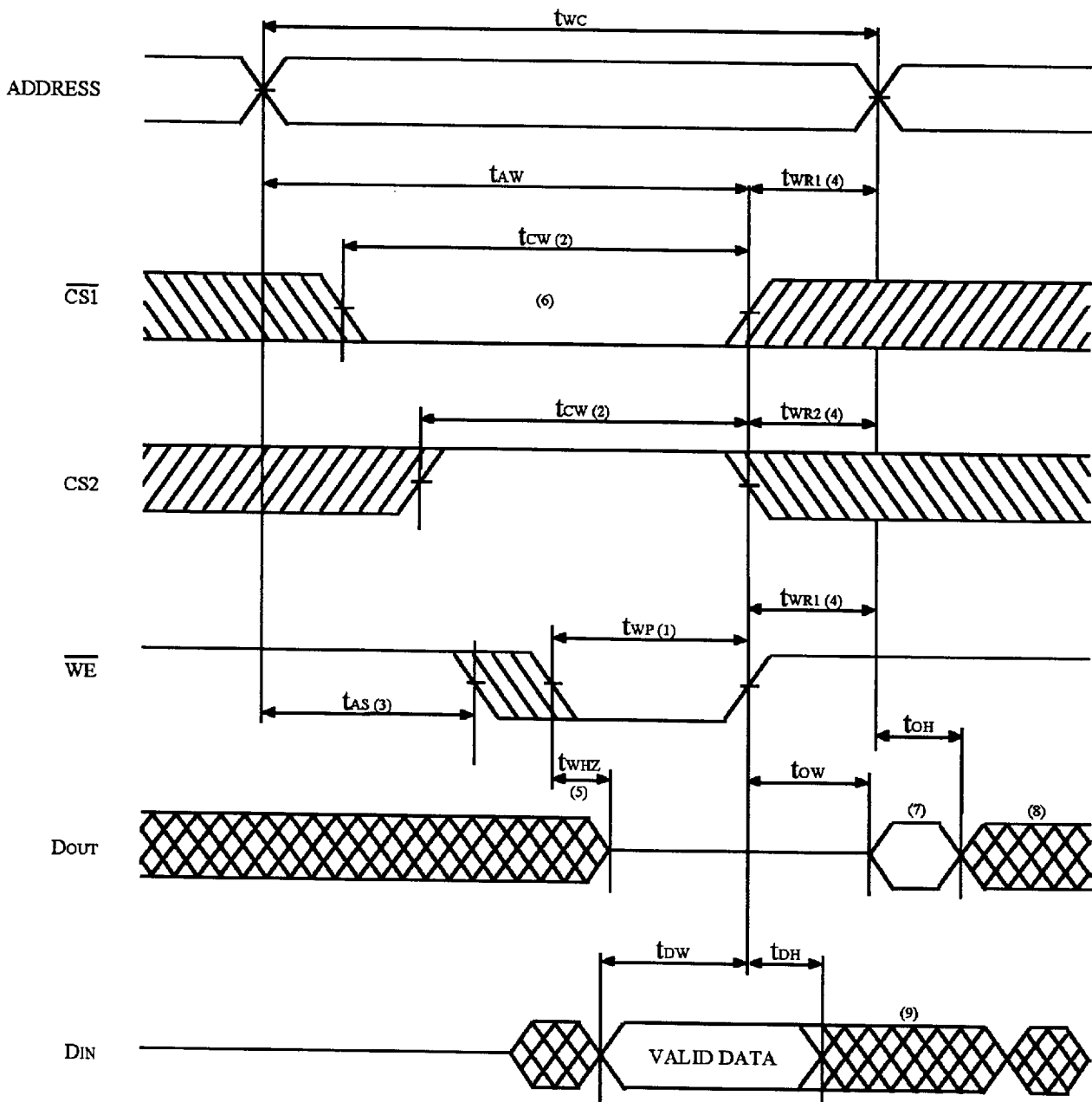


Note : 1) \overline{WE} is High for Read Cycle

Write Cycle (1) (\overline{OE} Controlled)



Write Cycle (2) (\overline{OE} Low Fix)



Notes:

1. A write occurs during the overlap of a low $\overline{CS1}$, a high CS2 and a low \overline{WE} . A write begins at the latest transition among $\overline{CS1}$ going low, CS2 going high and \overline{WE} going low. A write ends at the earliest transition among $\overline{CS1}$ going high, CS2 going low and \overline{WE} going high, t_{wp} is measured from the beginning of write to the end of write.
2. t_{cw} is measured from the later of $\overline{CS1}$ going low or CS2 going high to the end of write.
3. t_{as} is measured from the address valid to the beginning of write.
4. t_{wr} is measured from the end of write to the address change. t_{wr1} applies in case a write ends at $\overline{CS1}$ or \overline{WE} going high. t_{wr2} applies in case a write ends at CS2 going low.
5. During this period, I/O pins are in the output state, therefore the input signals of opposite phase to the outputs must not be applied.
6. If $\overline{CS1}$ goes low simultaneously with \overline{WE} going low or after \overline{WE} going low, the outputs remain in high impedance state.
7. D_{OUT} is the same phase of the latest written data in this write cycle.
8. D_{OUT} is the read data of next address.
9. If $\overline{CS1}$ is low and CS2 is high during this period, I/O pins are in the output state. Therefore, the input signals of opposite phase to the outputs must not be applied to them.

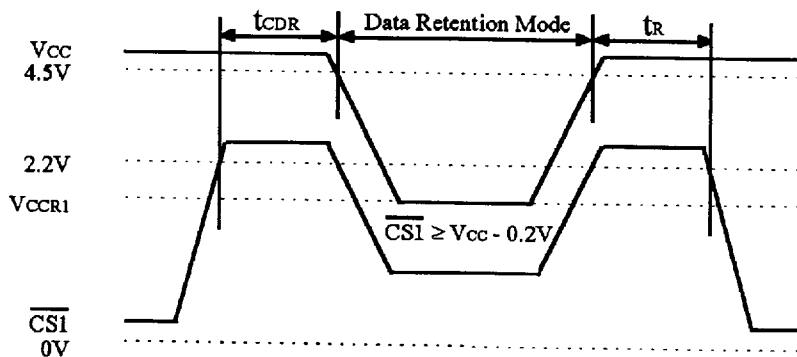
Data Retention Characteristics ($T_A = 0 \sim 70^\circ\text{C}$)

Symbol	Parameter		Test Conditions	Min	Typ	Max	Unit
V_{CCR}	Data Retention Supply Voltage	V_{CCR1}	$\overline{CS1} \geq V_{CC} - 0.2\text{V}$, $CS2 \geq V_{CC} - 0.2\text{V}$ or $CS2 \leq 0.2\text{V}$	2.0	-	5.5	V
		V_{CCR2}	$CS2 \leq 0.2\text{V}$	2.0	-	-	V
I_{CCR}	Data Retention Current	I_{CCR1}	$V_{CC} = 3.0\text{V}$, $\overline{CS1} \geq V_{CC} - 0.2\text{V}$, $CS2 \geq V_{CC} - 0.2\text{V}$ or $CS2 \leq 0.2\text{V}$	-	1	50*	μA
		I_{CCR2}	$V_{CC} = 3.0\text{V}$, $CS2 \leq 0.2\text{V}$	-	1	50*	μA
t_{CDR}	Chip Select to Data Retention Time	t_{CDR}	See Retention Waveform	0	-	-	ns
t_r	Operation Recovery Time	t_r		t_{rc}^{**}	-	-	ns

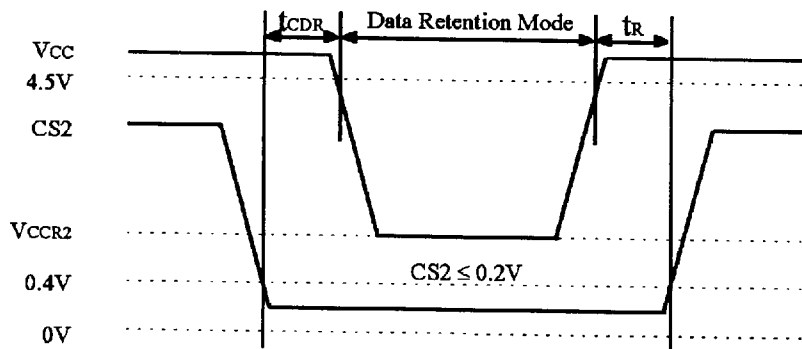
* $V_{IL \text{ min}} = -3\text{V}$, $1\mu\text{A max}$ at $T_A = 0 \sim 40^\circ\text{C}$

** t_{rc} = Read Cycle Time

• Low Vcc Data Retention Mode: (1) $\overline{CS1}$ Controlled



• Low Vcc Data Retention Mode: (2) CS2 Controlled

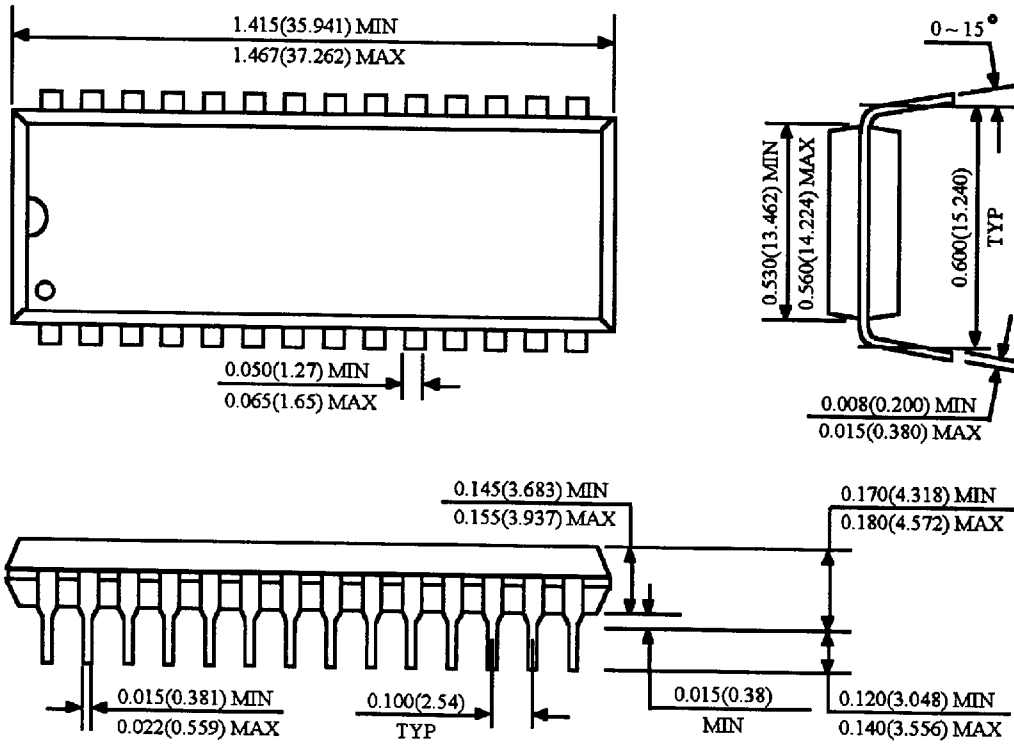


Notes: In Data Retention Mode, CS2 controls the Address, \overline{WE} , $\overline{CS1}$, \overline{OE} and D_{IN} buffer. If CS2 controls data retention mode, V_{IN} for these inputs can be in the high impedance state. If $\overline{CS1}$ controls the data retention mode, CS2 must satisfy either $CS2 \geq V_{CC} - 0.2\text{V}$ or $CS2 \leq 0.2\text{V}$. The other input levels (Address, \overline{WE} , \overline{OE} , I/O) can be in the high impedance state.

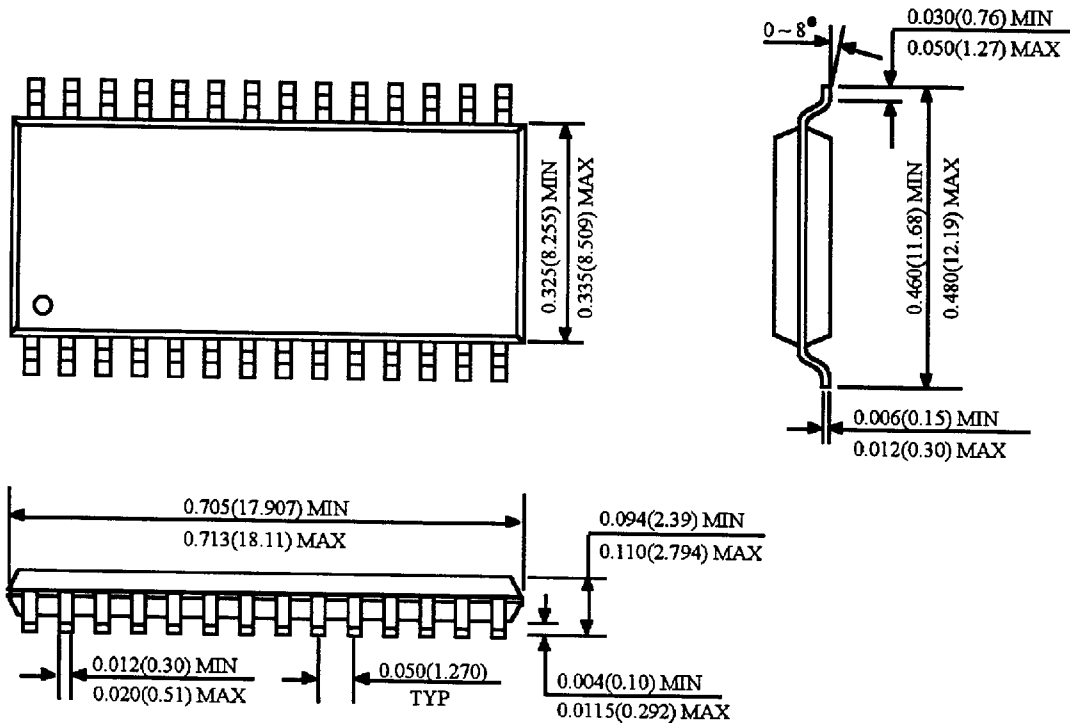
Package Dimensions

Unit: Inches (mm)

28 DIP - A



28 SOP - A



28 SKINNY DIP

Unit: Inches (mm)

